

Supplementary Materials

Solution-Processed Smooth Copper Thiocyanate Layer with Improved Hole Injection Ability for the Fabrication of Quantum Dot Light-Emitting Diodes

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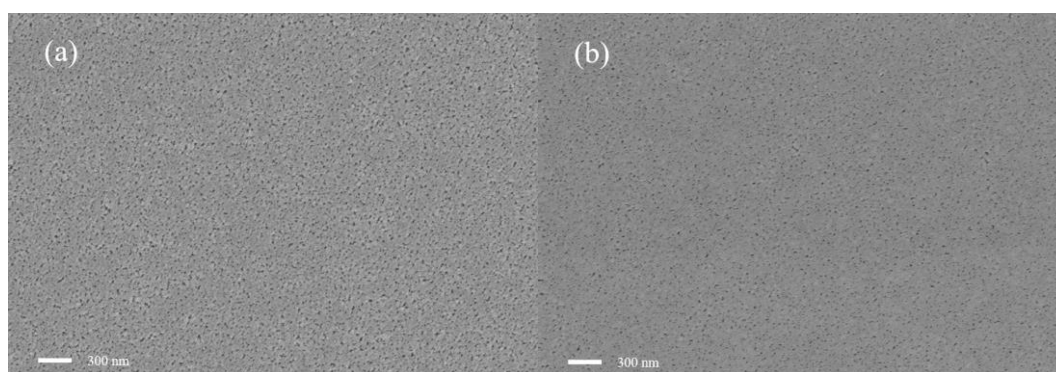


Figure S1. Top-view SEM micrographs of the (a) pristine and (b) F4TCNQ-doped CuSCN films.

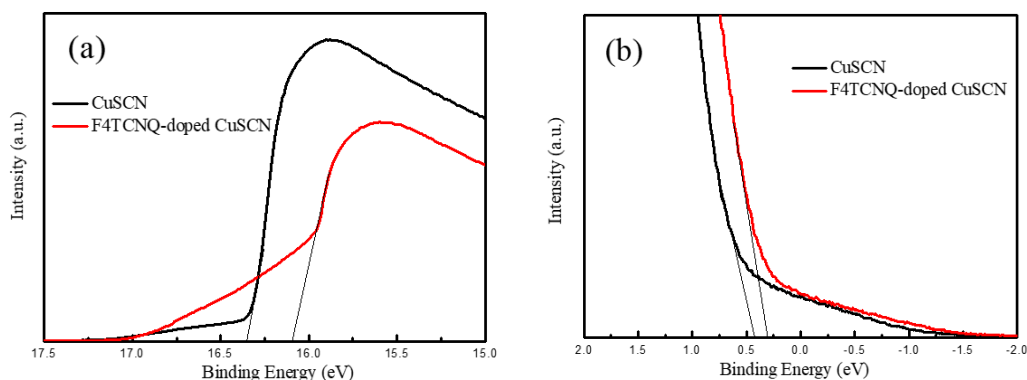


Figure S2. UPS spectra of the pristine and F4TCNQ-doped CuSCN layers in the (a) high-binding energy region and (b) valence-band edge.

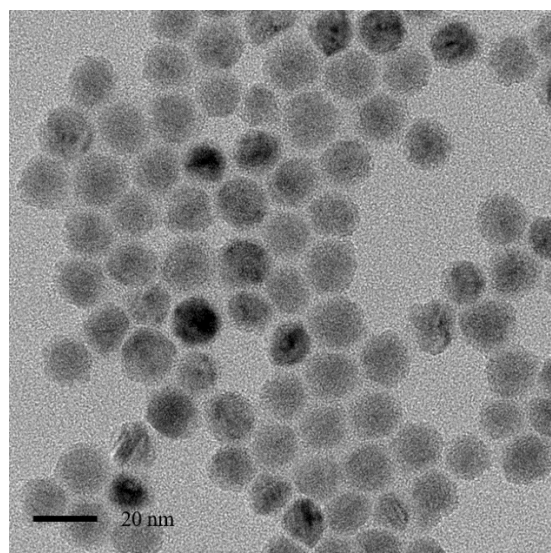


Figure S3. TEM image of CdSe QDs.

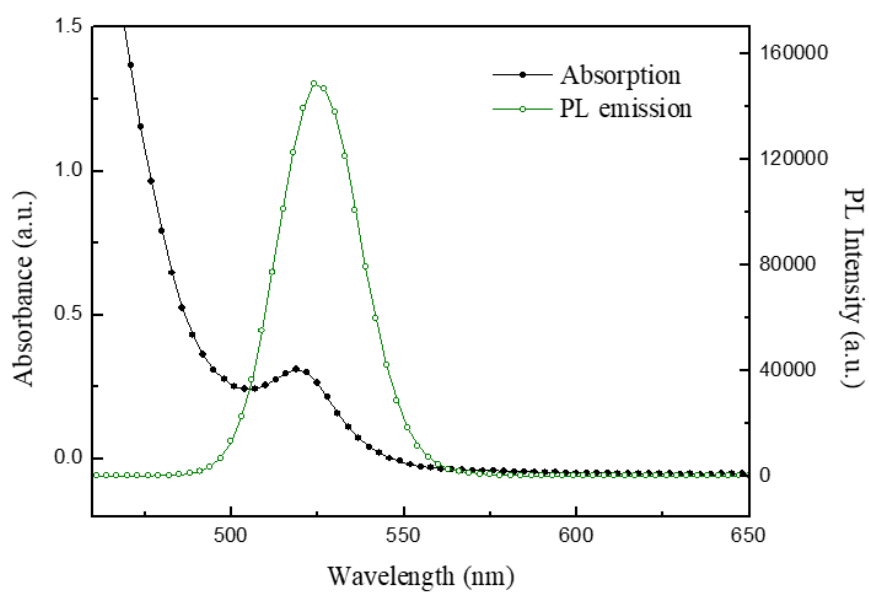


Figure S4. UV-vis absorption and PL emission spectra of CdSe QDs.